Ultra-Low Capacitance ESD Protection

The ESD7371 Series is designed to protect voltage sensitive components that require ultra-low capacitance from ESD and transient voltage events. Excellent clamping capability, low capacitance, high breakdown voltage, high linearity, low leakage, and fast response time make these parts ideal for ESD protection on designs where board space is at a premium. It has industry leading capacitance linearity over voltage making it ideal for RF applications. This capacitance linearity combined with the extremely small package and low insertion loss makes this part well suited for use in antenna line applications for wireless handsets and terminals.

Features

- Industry Leading Capacitance Linearity Over Voltage
- Low Capacitance (0.7 pF Max, I/O to GND)
- Stand-off Voltage: 5.3 V
- Low Leakage: < 1 nA
- Low Dynamic Resistance < 1 Ω
- IEC61000–4–2 Level 4 ESD Protection
- 1000 ESD IEC61000–4–2 Strikes ±8 kV Contact / Air Discharged
- SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

- RF Signal ESD Protection
- RF Switching, PA, and Antenna ESD Protection
- Near Field Communications
- USB 2.0, USB 3.0

MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
IEC 61000-4-2 (ESD) (Note 1)		20	kV
IEC 61000-4-5 (ESD) (Note 2)		3.0	А
Total Power Dissipation (Note 3) @ $T_A = 25^{\circ}C$ Thermal Resistance, Junction-to-Ambient	$P_D \\ R_{\theta J A}$	300 400	mW °C/W
Junction and Storage Temperature Range	T _J , T _{stg}	–55 to +150	°C
Lead Solder Temperature – Maximum (10 Second Duration)	ΤL	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

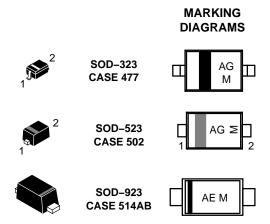
- 1. Non-repetitive current pulse at $T_A = 25^{\circ}C$, per IEC61000-4-2 waveform.
- 2. Non-repetitive current pulse at $T_A = 25^{\circ}C$, per IEC61000-4-5 waveform.
- 3. Mounted with recommended minimum pad size, DC board FR-4

See Application Note AND8308/D for further description of survivability specs.

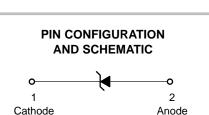


ON Semiconductor®

http://onsemi.com



X, XX = Specific Device Code M = Date Code



ORDERING INFORMATION

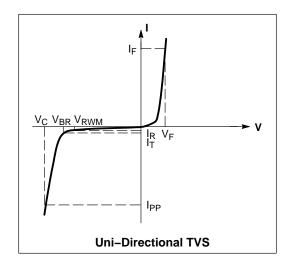
See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

ELECTRICAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

	,
Symbol	Parameter
I _{PP}	Maximum Reverse Peak Pulse Current
V _C	Clamping Voltage @ IPP
V _{RWM}	Working Peak Reverse Voltage
I _R	Maximum Reverse Leakage Current @ V _{RWM}
V _{BR}	Breakdown Voltage @ I _T
Ι _Τ	Test Current

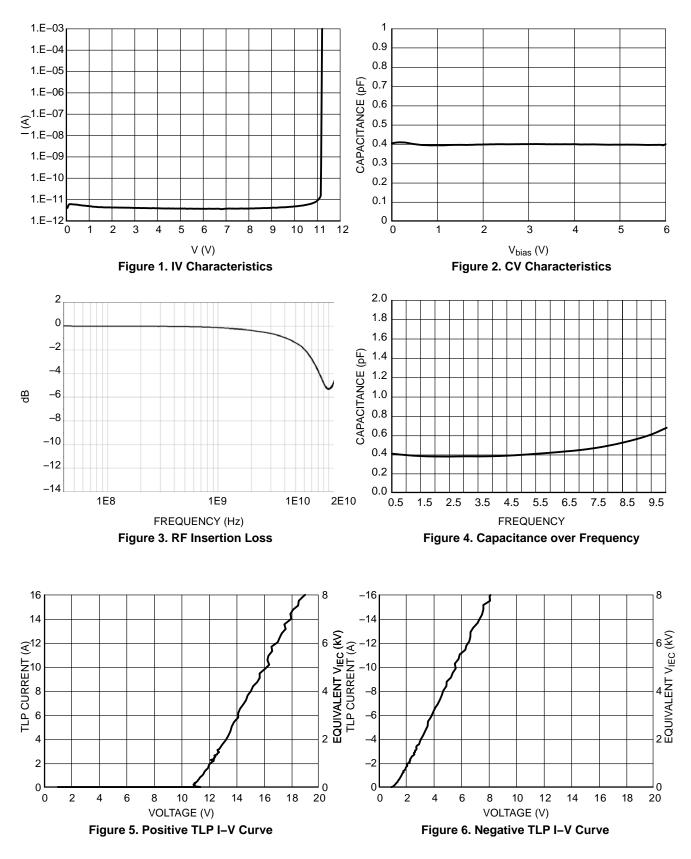
*See Application Note AND8308/D for detailed explanations of datasheet parameters.



ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Reverse Working Voltage	V _{RWM}				5.3	V
Breakdown Voltage (Note 4)	V _{BR}	I _T = 1 mA	7.0			V
Reverse Leakage Current	I _R	V _{RWM} = 5.3 V		< 1.0	50	nA
Clamping Voltage (Note 5)	V _C	I _{PP} = 1 A		11	15	V
Clamping Voltage (Note 5)	V _C	I _{PP} = 3 A		14	20	V
Junction Capacitance	CJ	$V_R = 0 V$, f = 1 MHz $V_R = 0 V$, f < 1 GHz		0.43 0.39	0.7 0.7	pF
Dynamic Resistance	R _{DYN}	TLP Pulse		0.45		Ω

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 4. Breakdown voltage is tested from pin 1 to 2 and pin 2 to 1. 5. Non-repetitive current pulse at $T_A = 25^{\circ}$ C, per IEC61000–4–5 waveform.



IEC 61000-4-2 Spec.

Level	Test Volt- age (kV)	First Peak Current (A)	Current at 30 ns (A)	Current at 60 ns (A)
1	2	7.5	4	2
2	4	15	8	4
3	6	22.5	12	6
4	8	30	16	8

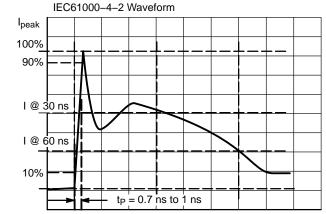


Figure 7. IEC61000-4-2 Spec

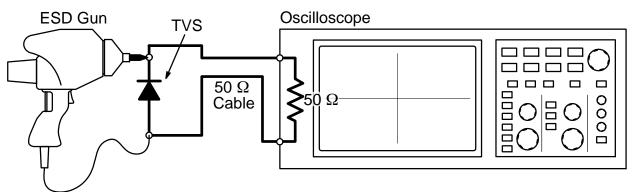


Figure 8. Diagram of ESD Clamping Voltage Test Setup

The following is taken from Application Note AND8308/D – Interpretation of Datasheet Parameters for ESD Devices.

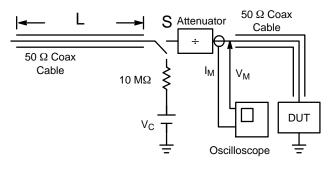
ESD Voltage Clamping

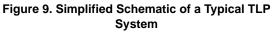
For sensitive circuit elements it is important to limit the voltage that an IC will be exposed to during an ESD event to as low a voltage as possible. The ESD clamping voltage is the voltage drop across the ESD protection diode during an ESD event per the IEC61000-4-2 waveform. Since the IEC61000-4-2 was written as a pass/fail spec for larger systems such as cell phones or laptop computers it is not clearly defined in the spec how to specify a clamping voltage at the device level. ON Semiconductor has developed a way to examine the entire voltage waveform across the ESD protection diode over the time domain of an ESD pulse in the form of an oscilloscope screenshot, which can be found on the datasheets for all ESD protection diodes. For more information on how ON Semiconductor creates these screenshots and how to interpret them please refer to AND8307/D.

Transmission Line Pulse (TLP) Measurement

Transmission Line Pulse (TLP) provides current versus voltage (I–V) curves in which each data point is obtained

from a 100 ns long rectangular pulse from a charged transmission line. A simplified schematic of a typical TLP system is shown in Figure 9. TLP I–V curves of ESD protection devices accurately demonstrate the product's ESD capability because the 10s of amps current levels and under 100 ns time scale match those of an ESD event. This is illustrated in Figure 10 where an 8 kV IEC 61000–4–2 current waveform is compared with TLP current pulses at 8 A and 16 A. A TLP I–V curve shows the voltage at which the device turns on as well as how well the device clamps voltage over a range of current levels.





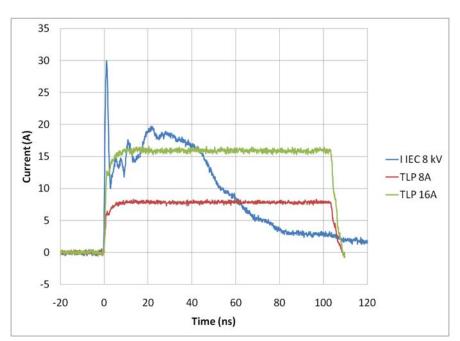


Figure 10. Comparison Between 8 kV IEC 61000-4-2 and 8 A and 16 A TLP Waveforms

ORDERING INFORMATION

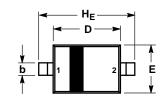
Device	Package	Shipping [†]
ESD7371HT1G, SZESD7371HT1G*	SOD-323 (Pb-Free)	3000 / Tape & Reel
ESD7371XV2T1G, SZESD7371XV2T1G*	SOD-523 (Pb-Free)	3000 / Tape & Reel
ESD7371P2T5G, SZESD7371P2T5G*	SOD-923 (Pb-Free)	8000 / Tape & Reel

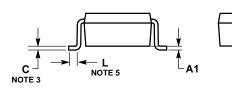
+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
 *SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP

Capable.

PACKAGE DIMENSIONS

SOD-323 CASE 477-02 **ISSUE H**





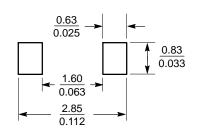


NOTES:
 DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLING DIMENSION: MILLIMETERS.
 LEAD THICKNESS SPECIFIED PER L/F DRAWING WITH SOLDER PLATING.
 DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
 DIMENSION L IS MEASURED FROM END OF RADIUS.

•	DIMENSION L IS MEASURED FROM END OF RADIUS								
		MILLIMETERS INCHES					5		
	DIM	MIN	NOM	MAX	MIN	NOM	MAX	1	
	Α	0.80	0.90	1.00	0.031	0.035	0.040		
	A1	0.00	0.05	0.10	0.000	0.002	0.004		
				_	0	000 05	-	1	

Α	0.80	0.90	1.00	0.031	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A3	0.15 REF			0.006 REF		
b	0.25	0.32	0.4	0.010	0.012	0.016
С	0.089	0.12	0.177	0.003	0.005	0.007
D	1.60	1.70	1.80	0.062	0.066	0.070
Е	1.15	1.25	1.35	0.045	0.049	0.053
L	0.08			0.003		
He	2 30	2 50	2 70	0 090	0.098	0 105

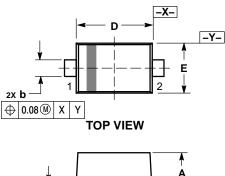
SOLDERING FOOTPRINT*

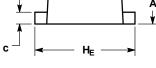


*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

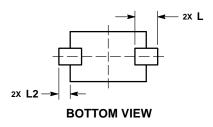
PACKAGE DIMENSIONS

SOD-523 CASE 502 ISSUE E



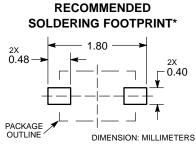






- NOTES:
 DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 CONTROLLING DIMENSION: MILLIMETERS.
 MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- DASE MALERIAL. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PRO-TRUSIONS, OR GATE BURRS. 9.

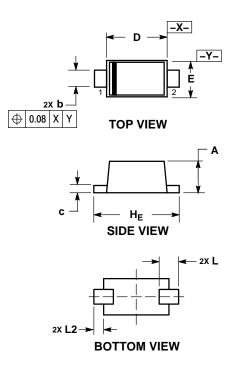
	MILLIMETERS					
DIM	MIN NOM MAX					
Α	0.50	0.60	0.70			
b	0.25	0.30	0.35			
С	0.07	0.14	0.20			
D	1.10	1.20	1.30			
E	0.70	0.80	0.90			
ΗE	1.50	1.60	1.70			
L	0.30 REF					
L2	0.15 0.20 0.2					



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

SOD-923 CASE 514AB ISSUE C

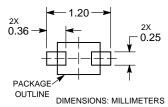


NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 - CONTROLLING DIMENSION: MILLIMETERS. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH
- MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PRO-TRUSIONS, OR GATE BURRS.

	MILLIMETERS				INCHES	;
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.34	0.37	0.40	0.013	0.015	0.016
b	0.15	0.20	0.25	0.006	0.008	0.010
С	0.07	0.12	0.17	0.003	0.005	0.007
D	0.75	0.80	0.85	0.030	0.031	0.033
E	0.55	0.60	0.65	0.022	0.024	0.026
HE	0.95	1.00	1.05	0.037	0.039	0.041
L	0.19 REF			0	.007 RE	F
L2	0.05	0.10	0.15	0.002	0.004	0.006

SOLDERING FOOTPRINT*



See Application Note AND8455/D for more mounting details

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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